



PATENT

Docket No.: M4065.0139/P139-A

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Cem Basceri

Application No.: 09/633,132

Filed: August 4, 2000

For: METHOD FOR IMPROVING THE
SIDEWALL STOICHIOMETRY OF
THIN FILM CAPACITORS

Box AF
Commissioner for Patents
Washington, D.C. 20231

Group Art Unit: 2815

Examiner: E. Lee

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A. H. H. H.
J. Mcmillen
12/3/02

Entered
J. Mcmillen
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JC 2800 MAIL ROOM

AMENDMENT AFTER FINAL

Dear Sir:

In response to the Office Action dated August 26, 2002, please amend the above-identified U.S. patent application as follows:

In the Claims:

Please replace claims 39, 48, and 74 with amended claims 39, 48, and 74 as follows:

39. (Fourth Amended) A capacitor comprising:

a material layer having a first level and a second level, said first and second levels being connected by at least two sidewall regions between said first and second levels; and

a post deposition doped BST high dielectric constant thin film material formed at least on both sidewall regions;